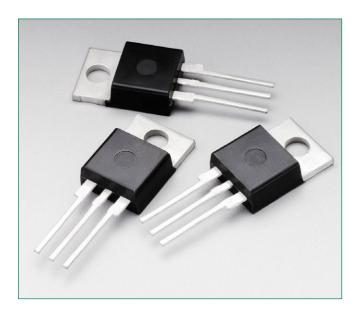


# MAC16HCDG, MAC16HCMG, MAC16HCNG

**Thyristors** 





#### **Description**

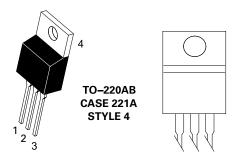
Designed primarily for full-wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full-wave, silicon gate-controlled devices are needed.

#### **Features**

- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS at 80°C

- High Surge Current Capability – 150 Amperes
- Industry Standard TO-220
   Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- These Devices are Pb-Free and are RoHS Compliant

#### **Pin Out**



# **Functional Diagram**



#### **Additional Information**







Samples



# Maximum Ratings (T<sub>J</sub> = 25°C unless otherwise noted)

**Thyristors** 

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (- 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	MAC16HCD MAC16HCM MAC16HCN	V <sub>DRM</sub> ,	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 Hz, T <sub>C</sub> = 80°C)		I <sub>T (RMS)</sub>	16	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 125°C)		I <sub>TSM</sub>	150	А
Circuit Fusing Consideration (t = 8.3 ms)		l²t	93	A²sec
Peak Gate Power ( $T_c = +80^{\circ}\text{C}$ , Pulse Width = 1.0 $\mu$ s)		P <sub>GM</sub>	20	W
Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}$ C)		$P_{G(AV)}$	0.5	W
Operating Junction Temperature Range		T <sub>J</sub>	-40 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied.

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Pur 10 seconds	poses, 1/8" from case for	T <sub>L</sub>	260	°C

#### Electrical Characteristics - OFF (T, = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	0.01	m A
$(V_D = V_{DRM} = V_{RRM})$ ; Gate Open)	T <sub>J</sub> = 125°C	IRRM	-	-	2.0	mA mA

#### Electrical Characteristics - ON (T<sub>1</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On-State Voltage (Note 2) (I <sub>TM</sub> = ±21 A Peak)		V <sub>TM</sub>	-	-	1.6	V
Gate Trigger Current	MT2(+), G(+)		10	16	50	
(Continuous dc)	MT2(+), G(-)	I <sub>GT</sub>	10	18	50	mA
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		10	22	50	
Gate Trigger Voltage	MT2(+), G(+)	0.5	0.75	1.5		
(Continuous dc)	MT2(+), G(-)	V <sub>GT</sub>	0.5	0.72	1.5	V
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		0.5	0.82	1.5	
	MT2(+), G(+)		-	33	60	
Latching Current $(V_D = 24 \text{ V}, I_C = 35 \text{ mA})$	MT2(+), G(-)	V <sub>GD</sub>	_	36	80	V
, b , G ,	MT2(-), G(-)		_	33	50	
Holding Current ( $V_D = 12 V_{dc'}$ Gate Open, Initiating Current = ±200 mA))		I <sub>H</sub>	-	20	50	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



# **Dynamic Characteristics**

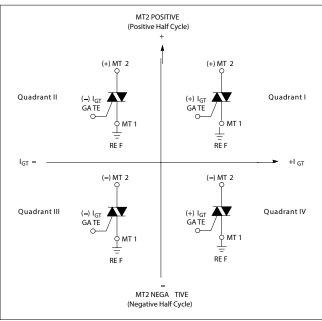
Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current ( $V_D = 400 \text{ V}$ , $I_{TM} = 6.0 \text{ A}$ , Commutating dV/dt = 24 V/ $\mu$ s, Gate Open, $I_J = 125^{\circ}$ C, $I_J = 125^{\circ}$	(di/dt)c	9.0	_	_	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated V_{DRM'} Exponential Waveform, Gate Open, T_J = 125°C)$	dv/dt	750	_	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 200 mA/µsec; f = 60 Hz	di/dt	_	_	10	

**Thyristors** 

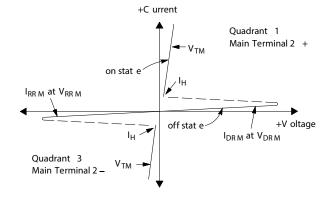
# **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I	Holding Current

# **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.
With in–phase signals (using standard AC lines) quadrants I and III are used



### Figure 1. Typical Gate Trigger Current vs Junction Temperature

**Thyristors** 

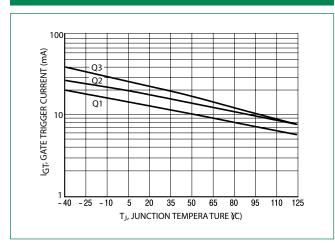


Figure 2. Typical Gate Trigger Voltage vs Junction Temperature

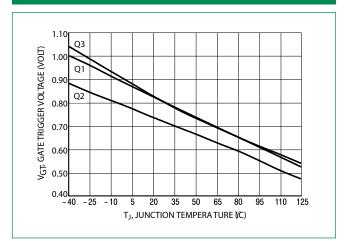


Figure 3. Typical Holding Current vs Junction Temperature

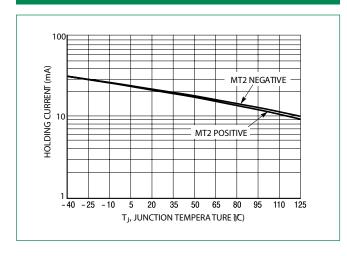


Figure 4. Typical Latching Current vs Junction Temperature

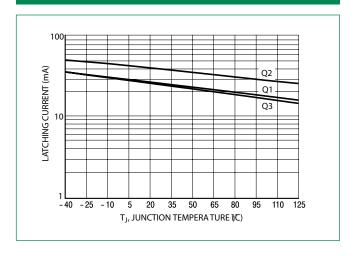
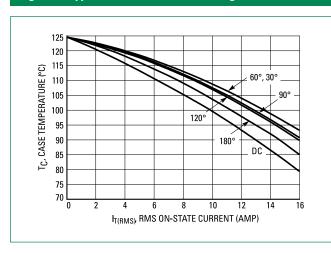
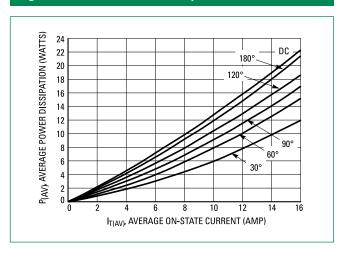


Figure 5. Typical RMS Current Derating



**Figure 6. On-State Power Dissipation** 



# **Figure 7. Typical On-State Characteristics**

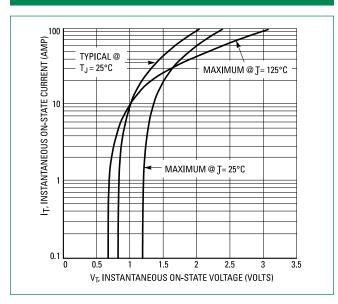
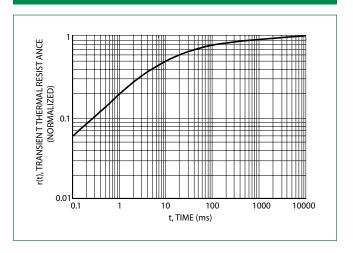
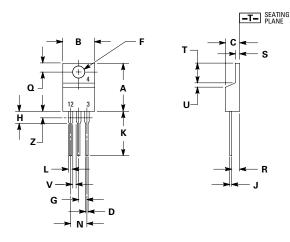


Figure 8. Typical Thermal Response

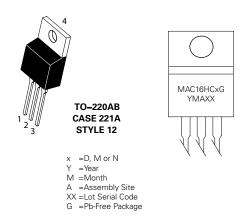




#### **Dimensions**



# **Part Marking System**



D:	Inc	hes	Millin	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

Pin Assignment		
1	Main Terminal 1	
2	Main Terminal 2	
3	Gate	
4	No Connection	

Oudouin	حادا د	
Orderin	g into	rmation

Device	Package	Shipping	
MAC16HCDG			
MAC16HCMG	TO-220 (Pb-Free)	500 Units/ Rail	
MAC16HCNG	(. 21100)		

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.